21 W × 4-Channel BTL Power IC

HITACHI

ADE-207-107 1st. Edition

Description

HA13150A is a four-channel BTL amplifier IC designed for car audio, featuring high output and low distortion, and applicable to digital audio equipment. It provides 21 W output per channel, with a 14.4 V power supply and at 10% distortion.

Functions

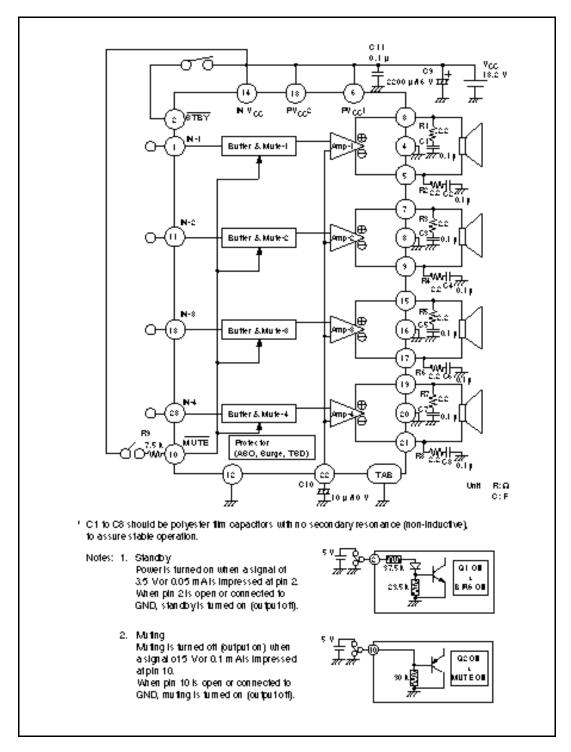
- Built-in standby circuit
- Built-in muting circuit
- Built-in protection circuits (surge, TSD, and ASO)

Features

- Requires few external parts
- Low distortion (total harmonic distortion = 0.01% at 3 W)
- Low noise (at Rg = 620Ω , noise is 0.15 mV (muting off) or 0.1 mV (muting on))
- Popping noise minimized
- Highly reliable current-limiting ASO protector keeps speakers safe from all kinds of trouble.
 Reliability is further enhanced by a fast-acting thermal shutdown protection circuit with on/off hysteresis.



Block Diagram



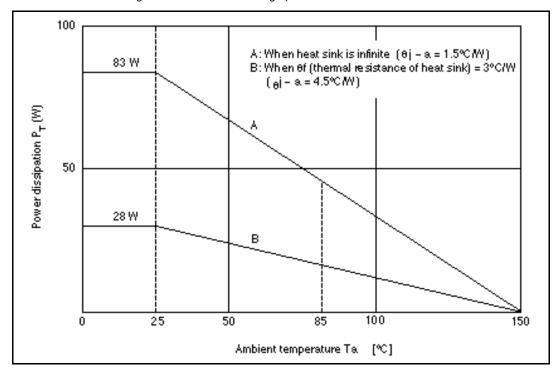
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item Symbol Rating Unit Remarks

				HA13150A
Operating supply voltage	V _{cc}	18	V	
Supply voltage when no signal *1	V _{cc} (DC)	26	V	
Peak supply voltage *2	V _{cc} (PEAK)	50	V	
Output current *3	I _o (PEAK)	4	А	
Power dissipation *4	P _T	83	W	
Junction temperature	Tj	150	$^{\circ}$	
Operating temperature	Topr	-30 to +85	°C	
Storage temperature	Tstg	-55 to +125	°C	

Notes: 1. Tolerance within 30 seconds

- 2. Tolerance in surge pulse waveform
- 3. Value per 1 channel
- 4. Value when attached on the infinite heat sink plate at Ta = 25°C. The derating carve is as shown in the graph below.



Electrical Characteristics (V $_{CC}$ = 13.2 V, f = 1 kHz, R_L = 4 $\Omega,~Rg$ = 620 $\Omega,~Ta$ = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Current when no signal	lq1	_	240	_	mA	Vin = 0
Output offset voltage	ΔVq	-250	0	+250	mV	
Gain	Gv	30.5	32	33.5	dB	
Gain difference between channels	ΔGv	-1.5	0	+1.5	dB	
Rated output power	Ро	_	18	_	W	$V_{CC} = 13.2 \text{ V}$ $R_L = 4 \Omega, \text{ THD} = 10\%$
Max output power	Pomax	_	30	_		$V_{CC} = 13.7 \text{ V}$ $R_L = 4 \Omega$, THD = Max
Total harmonic distortion	T.H.D	_	0.01	_	%	Po = 3 W
Output noise voltage	WBN	_	0.15	0.5	mVrms	Rg = 0Ω BW = $20 \text{ to } 20 \text{ kHz}$
Ripple rejection	SVR	_	55	_	dB	Rg = 600 Ω f = 120 Hz
Channel crosstalk	C.T	_	70	_	dB	Rg = 600Ω Vout = 0 dBm
Input impedance	Rin	_	25	_	kΩ	
Standby current	lq2	_	_	200	μΑ	
Standby control voltage (high)	$V_{\rm STH}$	3.5	_	V_{cc}	V	
Standby control voltage (low)	$V_{\mathtt{STL}}$	0	_	1.5	V	
Muting control voltage (high)	V_{MH}	3.5	_	V _{cc}	V	
Muting control voltage (low)	V _{ML}	0	_	1.5	V	
Muting attenuation	A _{TTM}		70		dB	Vout = 0 dBm

Pin Explanation

Pin No.	Symbol	Functions	Input Impedance	DC Voltage	Equivalence Circuit
1	IN1	CH1 INPUT	25 kΩ (Typ)	0 V	1 w w k x x x x x x x x x x x x x x x x x
11	IN2	CH2 INPUT			
13	IN3	CH3 INPUT			
23	IN4	CH4 INPUT			
2	STBY	Standby control	90 kΩ (at Trs. cutoff)	_	23.5 k
3	OUT1 (+)	CH1 OUTPUT		V _{cc} /2	3
5	OUT1 (–)				
7	OUT2 (+)	CH2 OUTPUT			
9	OUT2 (-)		<u> </u>		
15	OUT3 (+)	CH3 OUTPUT			
17	OUT3 (-)	CLIA OLITPLIT			
19	OUT4 (+)	CH4 OUTPUT			
10	OUT4 (–)	Muting control	25 kO (Typ)		
	MUTE	Muting control	25 kΩ (Typ)	_	10 \$25 k

Pin Explanation (cont)

Pin No.	Symbol	Functions	Input Impedance	DC Voltage	Equivalence Circuit
22	RIPPLE	Bias stability	_	V _{cc} /2	
6	PV _{cc} 1	Power of output stage	_	V _{cc}	_
18	PV _{cc} 2				
14	INV_CC	Power of input stage	_	V_{cc}	_
4	CH1 GND	CH1 power GND	_	_	_
8	CH2 GND	CH2 power GND	_		
16	CH3 GND	CH3 power GND	_		
20	CH4 GND	CH4 power GND	-		
12	IN GND	Input signal GND		_	_

Point of Application Board Design

- 1. Notes on Application board's pattern design
- For increasing stability, the connected line of V_{CC} and OUTGND is better to be made wider and lower impedance.
- For increasing stability, it is better to place the capacitor between V_{CC} and GND (0.1 μF) close to IC.
- For increasing stability, it is better to place C1 to C8 and R1 to R8, which are for stopping oscillation, close to IC.
- It is better to place the grounding of resistor (Rg), between input line and ground, close to INGND (Pin 12) because if OUTGND is connected to the line between Rg and INGND, THD will become worse due to current from OUTGND.

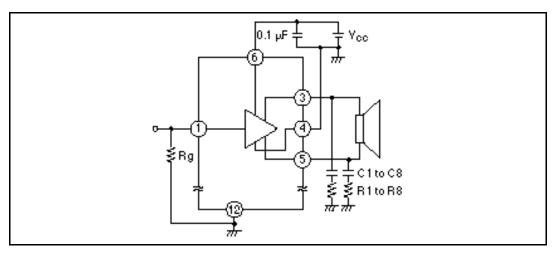


Figure 1 Notes on Application Board's Pattern Design

2. How to reduce the popping noise by Muting circuit

At normal operating circuit, Muting circuit operates at high speed under 1 μs.

In case popping noise becomes a problem, it is possible to reduce the popping noise by connecting capacitor, which determines the switching time constant, between pin 10 and GND. (Following figure 2)

We recommend value of capacitor greater then 1 µF.

Also transitional popping noise can be reduced sharply by muting before V_{CC} and Standby are ON/OFF.

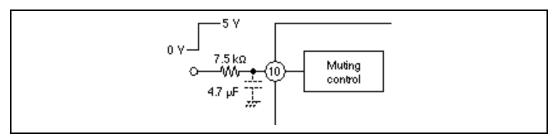
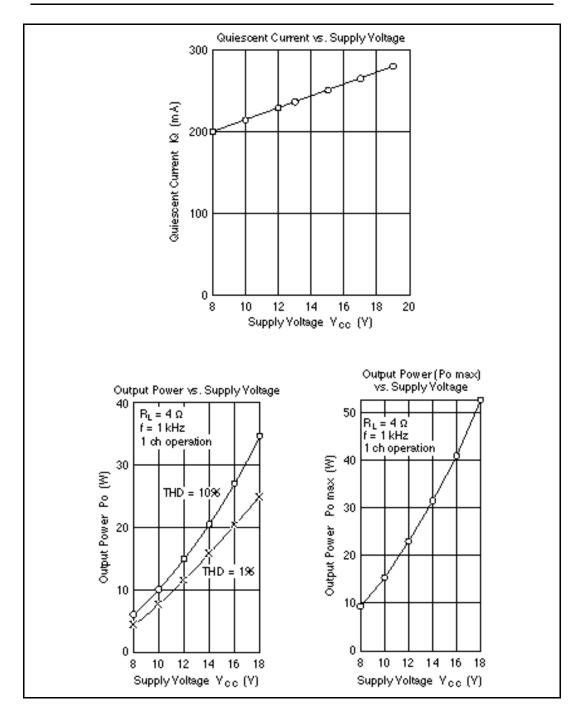
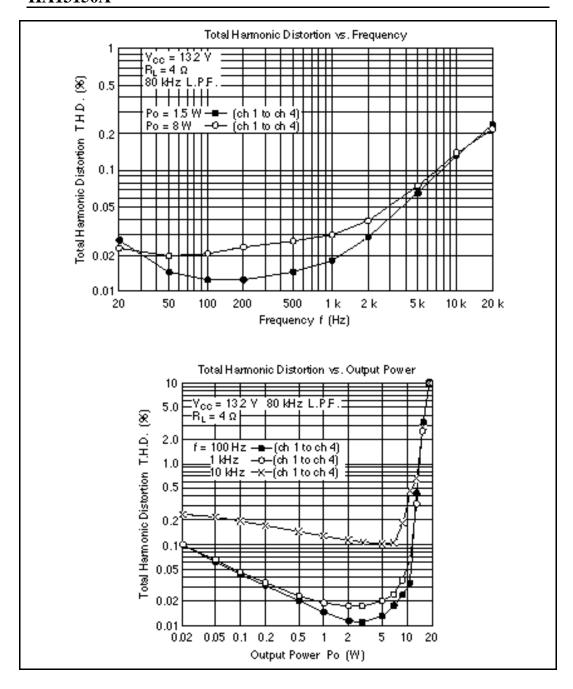


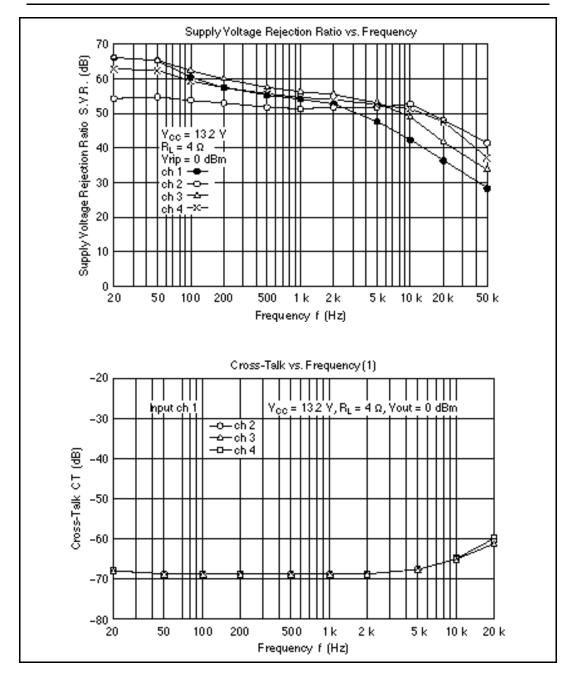
Figure 2 How to use Muting Circuit

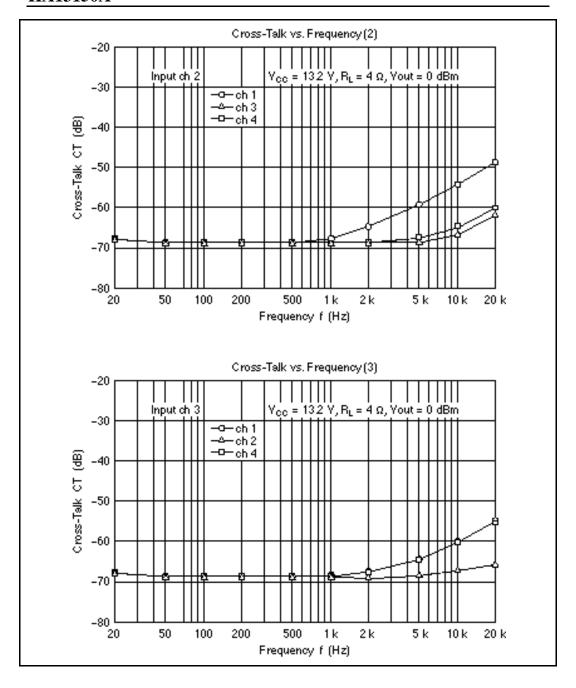
Table 1 Muting ON/OFF Time

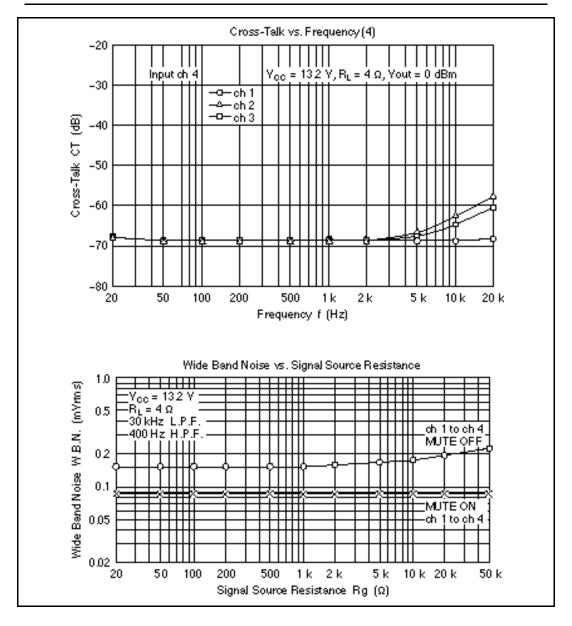
C (μF)	ON Time	OFF Time
nothing	under 1 µs	under 1 µs
0.47	2 ms	2 ms
4.7	19 ms	19 ms

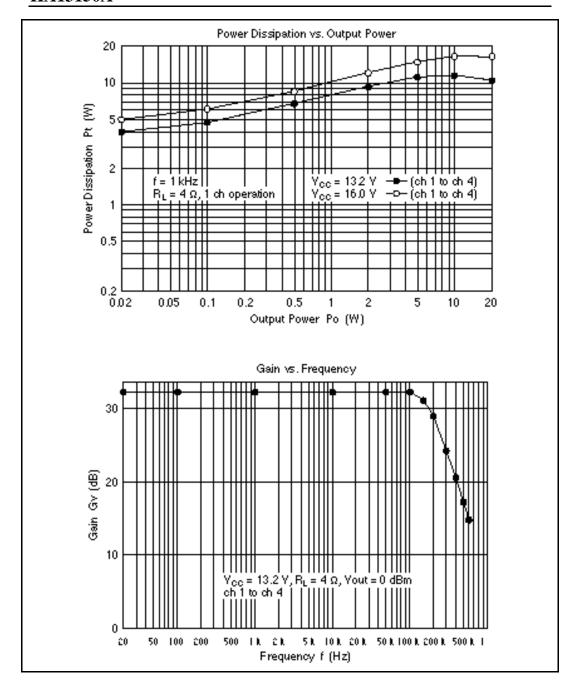












When using this document, keep the following in mind:

- 1. This document may, wholly or partially, be subject to change without notice.
- 2. All rights are reserved: No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without Hitachi's permission.
- 3. Hitachi will not be held responsible for any damage to the user that may result from accidents or any other reasons during operation of the user's unit according to this document.
- 4. Circuitry and other examples described herein are meant merely to indicate the characteristics and performance of Hitachi's semiconductor products. Hitachi assumes no responsibility for any intellectual property claims or other problems that may result from applications based on the examples described herein.
- 5. No license is granted by implication or otherwise under any patents or other rights of any third party or Hitachi, Ltd.
- 6. MEDICAL APPLICATIONS: Hitachi's products are not authorized for use in MEDICAL APPLICATIONS without the written consent of the appropriate officer of Hitachi's sales company. Such use includes, but is not limited to, use in life support systems. Buyers of Hitachi's products are requested to notify the relevant Hitachi sales offices when planning to use the products in MEDICAL APPLICATIONS.

HITACHI

Hitachi, Ltd.
Semiconductor & IC Dv.
Nepon Bidg. 26-2, Ohte-medii, Chiyode-ku, Tokyo 100, Japan Tet Tokyo (03) 3270-2111
Fex: (03) 3270-2100

For Author in formellon write to:

Hitechi Americe, Ltd. Semiconductor & IC Div. 2000 Sierre Point Perlavey Briebene, CA. 94005-4835 U.S.A. Toy AUS 500 2000

Tet 415-589-8300 Fex: 415-583-4207 Hitachi Burope SmbH
Bedtonic Componente Group
Continental Burope
Darrecher Streise 3
D-89522 Feldkirchen
München
Tet 089-9 94 80-0
Fex 089-9 20 30 00

Hitachi Burope Ltd.
Bedtronic Components Div.
Northern Burope Headquerters
Whitebrook Park
Lower Cook ham Road
Maidenhead
Berkshire SU68YA
Urited Kingdon
Tet 0628-585000
Fex: 0628-778222

Hitachi Asia Pta, Ltd 45 Collyer Quay \$20-00 Hitachi Tower Snappore 0404 Tet 595-2400 Fex: 595-4593

Hischi Asia (Hong Kong) Ltd. Unit 706, North Tower, World Finance Centre, Herbour City, Centron Road Teim She Teid, Kowloon Hang Kong Tet 27:359248 Fex: 27:308074

HITACHI